NEW PRODUCT

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D T_A = +25°C
-100V	250mΩ @ V_{GS} = -10V	-2.3A
	300mΩ @ V_{GS} = -4.5V	-2.1A

Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features and Benefits

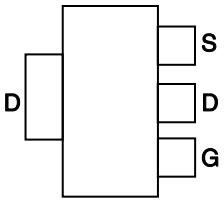
- Low Gate Drive
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

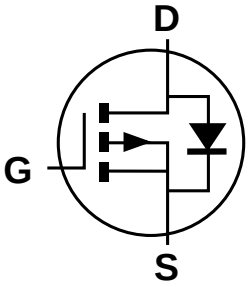
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.112 grams (Approximate)

SOT223

Top View



Pin Out - Top View



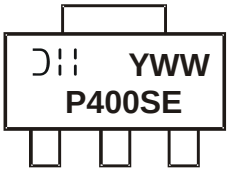
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
DMP10H400SE-13	Standard	SOT223	2,500 / Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



= Manufacturer's Marking
P400SE = Marking Code
YWW = Date Code Marking
Y or Y= Year (ex: 4 = 2014)
WW = Week (01 to 53)

NEW PRODUCT

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-100	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = -10V	Steady State	T_C = +25°C T_A = +25°C	I_D	-6.0 -2.3	A
Maximum Body Diode Forward Current (Note 5)			I_S	-1.9	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I_{DM}	-10	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	2.0	W
	T_A = +70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	62	°C/W
Total Power Dissipation (Note 5)	T_C = +25°C	P_D	13.7	W
Thermal Resistance, Junction to Case (Note 5)		$R_{\theta JC}$	9.1	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	-100	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = -80V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1.0	-2.2	-3.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	203	250	mΩ	V_{GS} = -10V, I_D = -5A
		—	241	300		V_{GS} = -4.5V, I_D =-5A
Diode Forward Voltage	V_{SD}	—	-0.9	-1.2	V	V_{GS} = 0V, I_S = -5A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	1239	—	pF	V_{DS} = -25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	42	—		
Reverse Transfer Capacitance	C_{rss}	—	28	—		
Gate Resistance	R_G	—	13	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	8.4	—	nC	V_{DS} = -60V, I_D = -5A
Total Gate Charge (V_{GS} = -10V)	Q_g	—	17.5	—		
Gate-Source Charge	Q_{gs}	—	2.8	—		
Gate-Drain Charge	Q_{gd}	—	3.2	—		
Turn-On Delay Time	$t_{D(ON)}$	—	9.1	—	ns	V_{DD} = -50V, R_G = 9.1Ω, I_D = -5A
Turn-On Rise Time	t_R	—	14.9	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	57.4	—		
Turn-Off Fall Time	t_F	—	34.4	—		
Body Diode Reverse Recovery Time	t_{RR}	—	25.2	—	ns	V_{GS} = 0V, I_S = -5A, dI/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	24.5	—	nC	V_{GS} = 0V, I_S = -5A, dI/dt = 100A/µs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to production testing.

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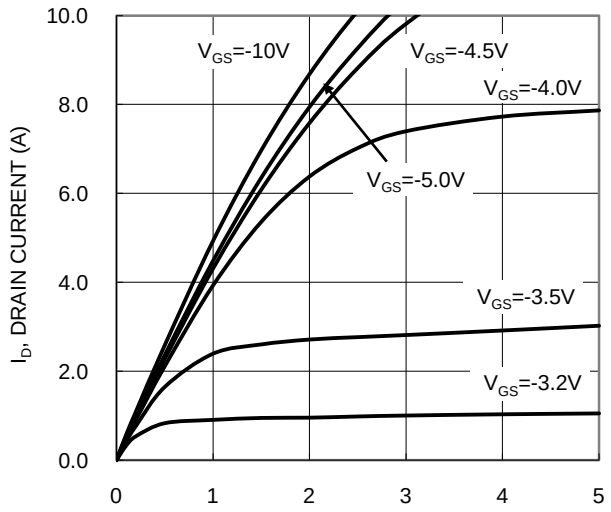

Figure 1. Typical Output Characteristic

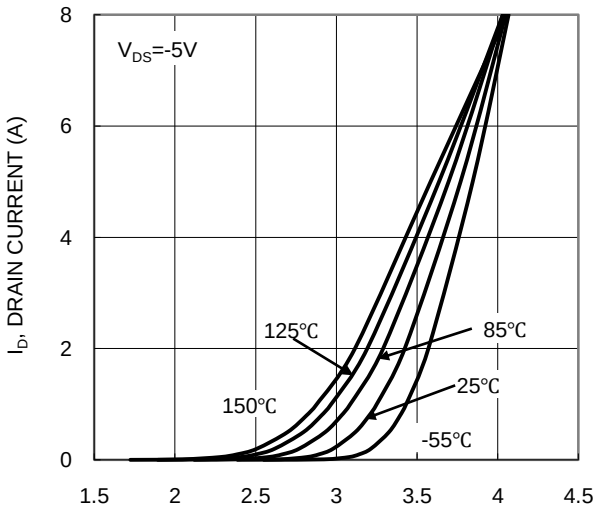

Figure 2. Typical Transfer Characteristic

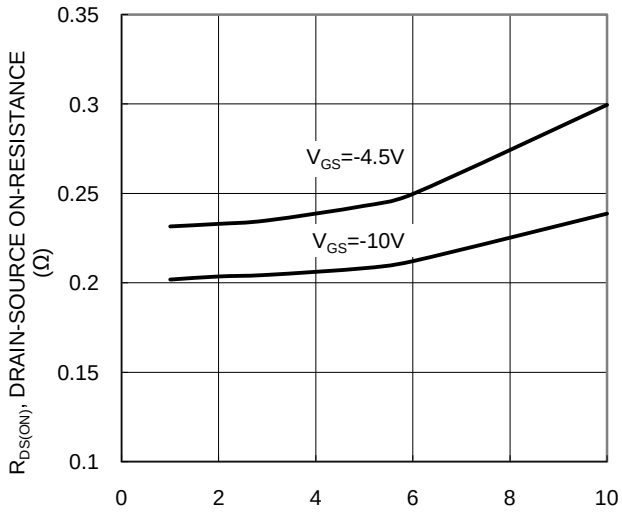

Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

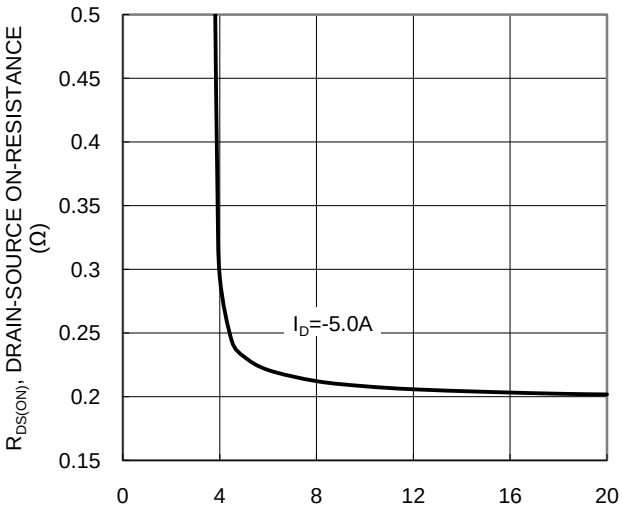

Figure 4. Typical Transfer Characteristic

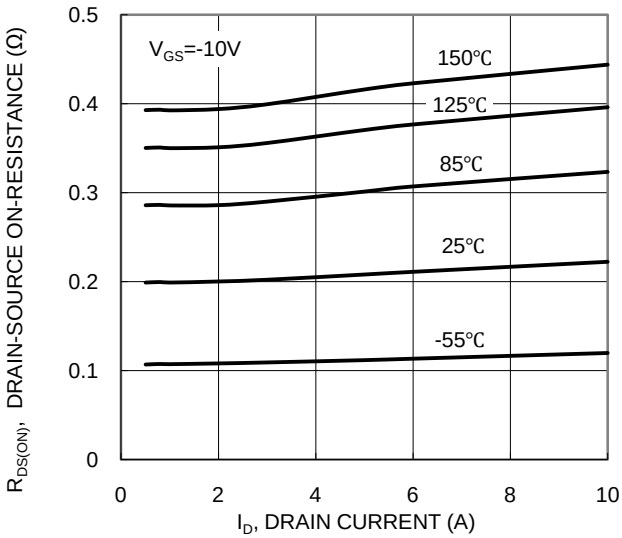

Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

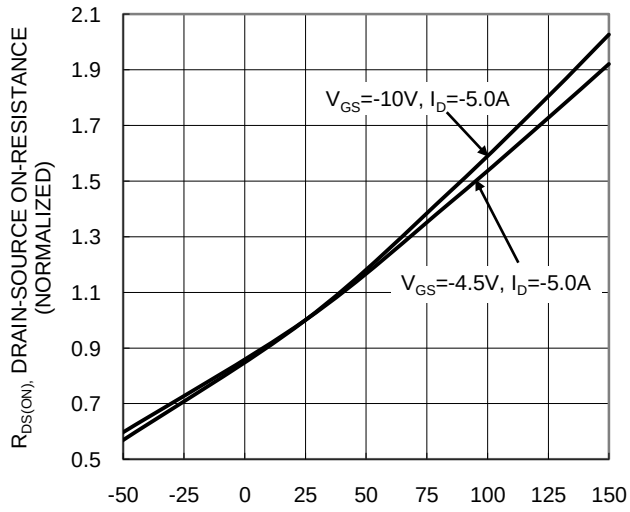

Figure 6. On-Resistance Variation with Junction Temperature

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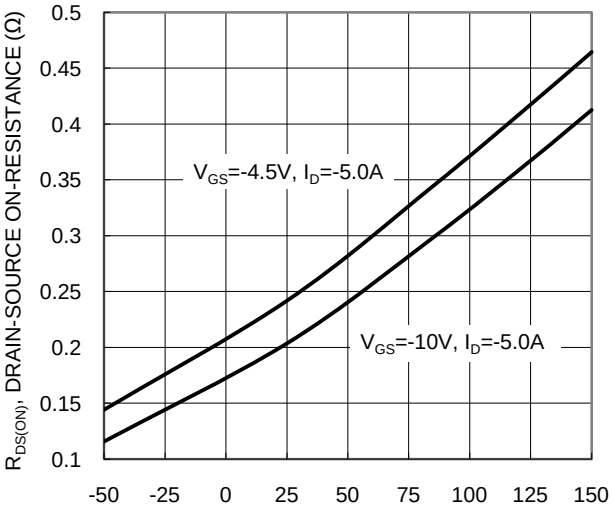

Figure 7. On-Resistance Variation with Junction Temperature

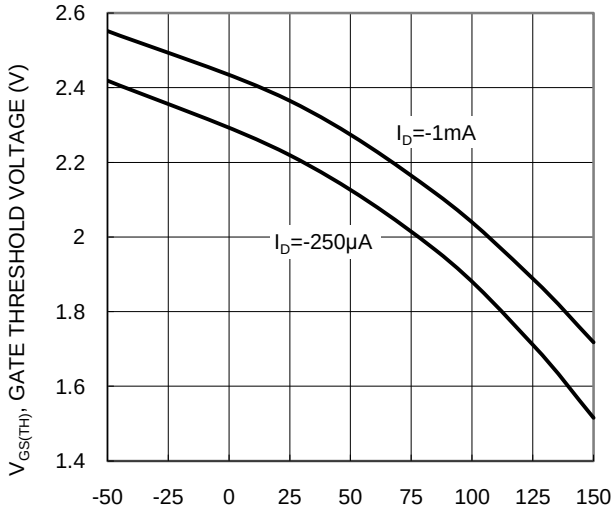

Figure 8. Gate Threshold Variation vs. Junction Temperature

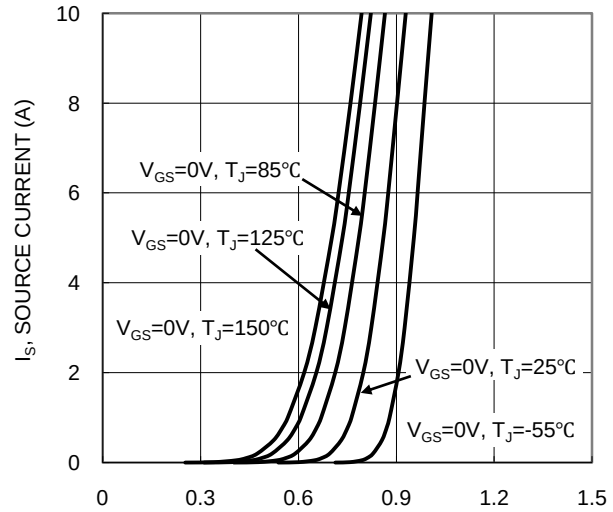

Figure 9. Diode Forward Voltage vs. Current

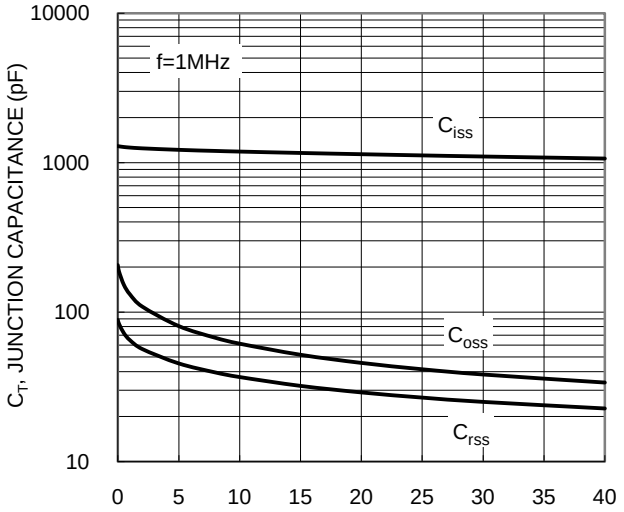

Figure 10. Typical Junction Capacitance

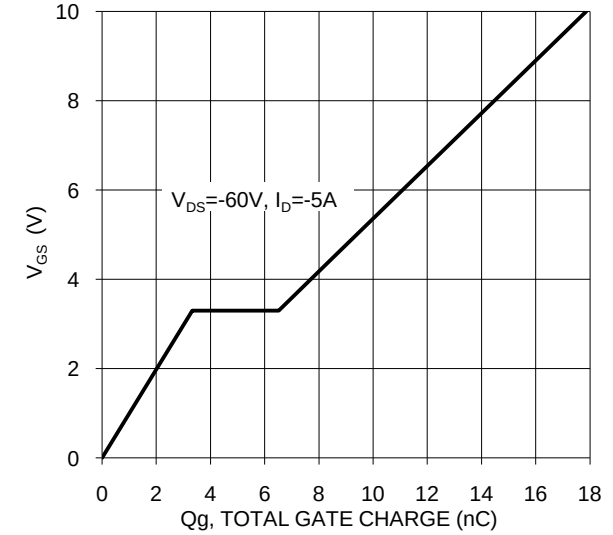

Figure 11. Gate Charge

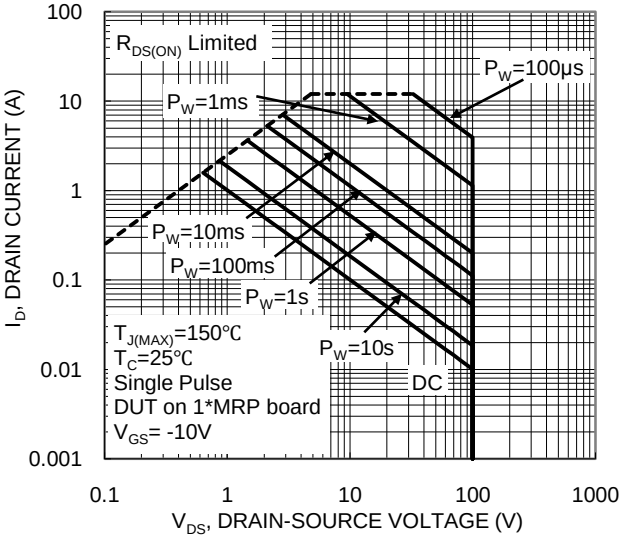

Figure 12. SOA, Safe Operation Area

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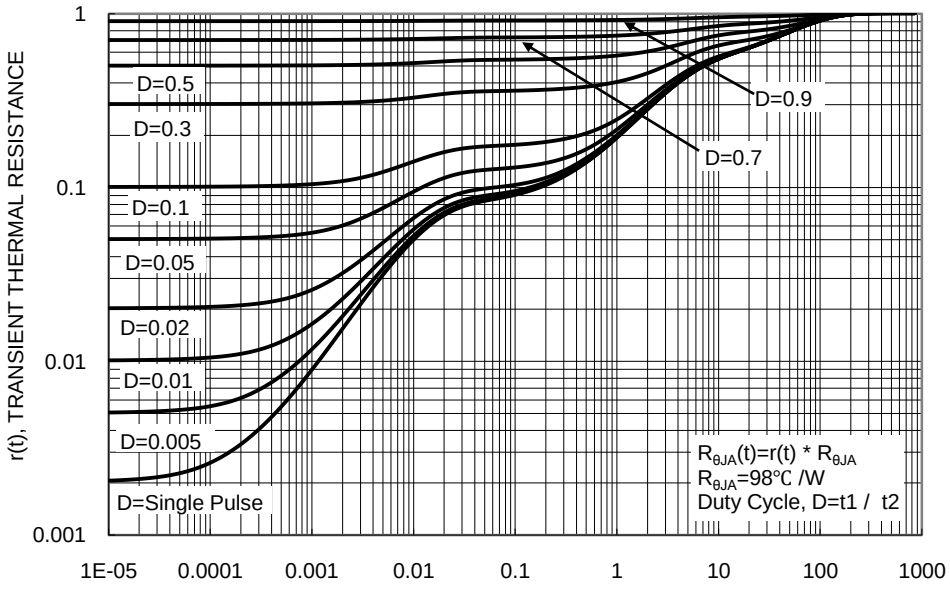
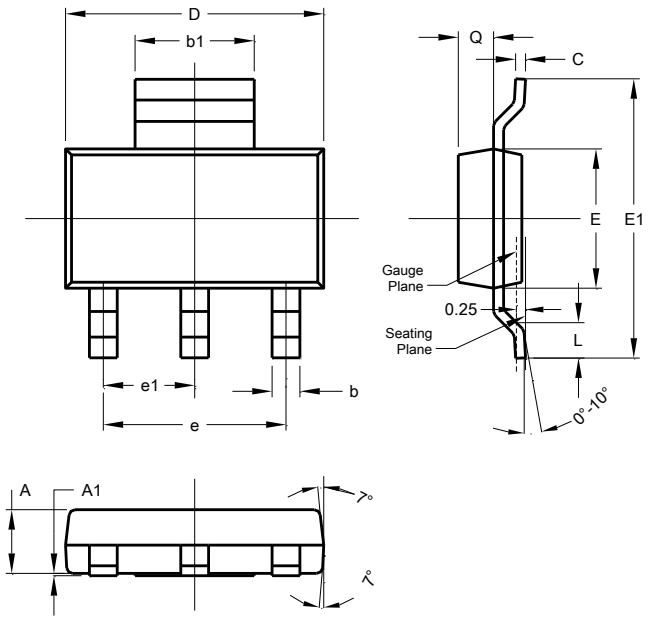


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

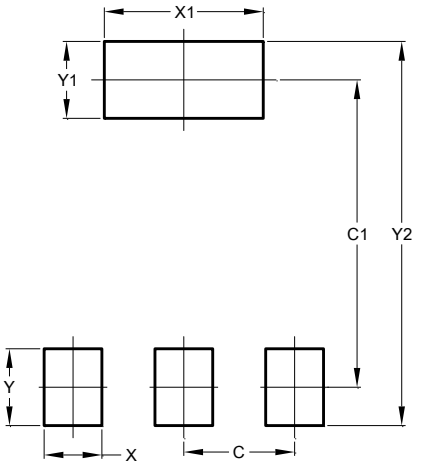


SOT223			
Dim	**Min**	**Max**	**Typ**
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

NEW PRODUCT

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00